

**In the Claims:**

**Claims 1-30 (canceled).**

**Claim 31 (previously presented):** A silicon integrated circuit fabricated using a method of removing excess interconnect material during fabrication of said silicon integrated circuit, said method of removing comprising the steps of:

dispensing a slurry including abrasive particles and chemical on a sample having said excess interconnect material;

polishing said sample with said slurry, using a polishing pad having a plurality of pits, to remove said excess interconnect material, wherein said abrasive particles and chemical become embedded into said plurality of pits of said polishing pad;

reducing said dispensing of said slurry after said polishing for a first period of time; and

polishing said sample using said polishing pad for a second period of time to remove said excess interconnect material.

**Claim 32 (previously presented):** The silicon integrated circuit of claim 31, wherein said step of reducing reduces said dispensing of said slurry to a stop.

**Claim 33 (previously presented):** The silicon integrated circuit of claim 31, wherein said silicon integrated circuit includes a metal gate fabricated with Atomic Layer Deposition (ALD) and said excess interconnect material is copper.

**Claim 34 (previously presented):** The silicon integrated circuit of claim 33, wherein said ALD includes Ta.

**Claim 35 (previously presented):** The silicon integrated circuit of claim 31, wherein said step of reducing occurs after a step of endpoint detection of said step of polishing said sample with said slurry, based on a thickness of said excess interconnect material.

**Claim 36 (previously presented):** The silicon integrated circuit of claim 35, wherein said thickness of said excess interconnect material is determined based on optical reflectivity.

**Claim 37 (previously presented):** The silicon integrated circuit of claim 31, said excess interconnect material is copper.

**Claim 38 (previously presented):** The silicon integrated circuit of claim 31, wherein said plurality of pits are created by abrading a polishing surface of said polishing pad with an abrasive disc.

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**Claim 39 (previously presented):** The silicon integrated circuit of claim 31, wherein said steps of polishing are performed at a pressure of about 1.5 psi.

**Claim 40 (previously presented):** The silicon integrated circuit of claim 31, wherein said steps of polishing are performed at a pressure of about 2.7 psi.